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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										外形	備考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{FE} h _{FE} * (Ω)	h _{FE} h _{FE} * (×10 ⁻⁴)	h _{FE} h _{FE} * (μS)	f _{αB} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 f_{αB} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
 - 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 ($T_a = 25^\circ\text{C}$)					電気的特性 ($T_a = 25^\circ\text{C}$)											外形	備考			
				V_{CBO} (V)	V_{EBO} (V)	I_C (mA)	P_C (mW)	T_j ($^\circ\text{C}$)	I_{CBO} 最大値 (μA)		直流又はパルス h_{FE}		バイアス		h_{fe}	h_{ie}	h_{ie}^*	h_{re}	h_{re}^*			h_{oe}	f_{ab}	C_{ob}
										$V_{CE(V)}$	$I_C(\text{mA})$	$V_{CB(V)}$	$I_E(\text{mA})$		Ω	$(\times 10^{-4})$	(μt)	(Mc)	(pF)	$h_{ie}(\text{real})^*$				
★	2SC1391	日立	PA	Si. T	300	4	100	6.5W ($T_c=25^\circ\text{C}$)	150	100	300	60	10	50	50	-20				25*	5	20*	153	
	" 1392																							
	" 1393	日電	RF. LN	Si. E	30	5	20	250	125	0.1	20	100	10	2	10	-3		NF=2dB ($f=200\text{MHz}$)	700*	C_{re} 0.35	$C_c \tau_{bb'}$ 10pS	138C		
	" 1394	"	RF. Conv. Mix. Osc	"	30	5	20	250	125	0.1	20	100	10	2	10	-3			700*	C_{re} 0.35	$C_c \tau_{bb'}$ 10pS	138C		
★	" 1395	"	"	Si. EP	30	5	20	250	125	0.1	12	100	10	5	10	-5			1100*	1.2	$C_c \tau_{bb'}$ 12pS	138		
★	" 1396	"	"	"	30	5	20	250	125	0.1	12	100	10	5	10	-5			1100*	1.2	$C_c \tau_{bb'}$ 12pS	138		
	" 1397																							
	" 1398	松下	RF. PA	Si. EP	70	5	2A	15W ($T_c=25^\circ\text{C}$)	150	1	40	130	5	1A	5	-500			150*	50	3*	268	2SA748 とコンプリ	
	" 1399	日電	AF	Si. E	100	5	50	250	125	0.05	100	600	3	0.5	6	-1			100*	2.7		138		
	" 1400	"	LN	Si. EPa	100	5	50	250	125	0.05	100	500	3	0.5	6	-1			100*	2.7	50*	138		
	" 1401	富士通	SW	Si. TMe	400	5	30A	200W ($T_c=25^\circ\text{C}$)	175	200	150	25	5	15A	5	-2A	$t_{on} < 4\mu\text{S}$, $t_f < 2.5\mu\text{S}$ $t_{off} < 4\mu\text{S}$		20*			191		
	" 1402	サンケン	PA	Si. TMe	140	6	8A	70W ($T_c=25^\circ\text{C}$)	150	1mA	140	60	4	3A	12	-500			10*	130	7*	102	2SA744 とコンプリ	
	" 1403	"	"	"	160	5	8A	70W ($T_c=25^\circ\text{C}$)	150	1mA	160	60	4	3A	12	-500			10*	130	7*	102	2SA745 とコンプリ	
	" 1404	松下	"	Si. EP	36	4	3.5A	50W ($T_c=25^\circ\text{C}$)	200	25mA	36	30	5	1A	5	-1A	$P_o = 18\text{W}$ ($f=470\text{MHz}$, $V_{cc}=12.5\text{V}$, $P_i=6.8\text{W}$)		1000*	55		229		
	" 1405	"	"	"	36	4	750	10W ($T_c=25^\circ\text{C}$)	175	50	20	40	10	100	10	-100	$P_o = 3.5\text{W}$, $C_{ce} = 10\text{pF}$ ($f=175\text{MHz}$, $V_{cc}=13.5\text{V}$, $P_i=0.35\text{W}$)		350*	13		227		
★	" 1406	"	"	"	30	5	1A	1W	135	0.1	20	160	10	500	10	-50			200*	11	3.5*	173	2SA751 とコンプリ	
★	" 1407	"	"	"	60	5	1A	1W	135	0.1	20	160	10	500	10	-50			200*	11	3.5*	173	2SA752 とコンプリ	
	" 1408																							
★	" 1409	日立	PA	Si. TMe	200	6	2A	12.5W ($T_c=25^\circ\text{C}$)	150	1	30	100	10	50	10	-50			20*	95	20	267		
★	" 1410	"	"	"	200	6	2A	12.5W ($T_c=25^\circ\text{C}$)	150	1	30	100	10	50	10	-50			20*	95	20	268		
	" 1411	富士通	SW	Si. EP (双方向)	6	6	50	200	150	0.1	5	100					$t_r < 300\text{nS}$, $t_f < 500\text{nS}$ $t_{off} < 600\text{nS}$			6		49C		
	" 1412	"	RF	Si. EP	45	3	150	600	150	0.5	20	70	10	40	10	-40			1500*	2.5	40	84B		
	" 1413	日立	SW	Si. T	1200	6	5A	50W ($T_c=25^\circ\text{C}$)	150	I_{CBO} 1mA	1200				15	-200	$t_f < 2.3\mu\text{S}$		4*	175		102	水平偏向用	
	" 1414	富士通	PA	Si. EP	40	3.5	2A	20W ($T_c=25^\circ\text{C}$)	175	400	20	80	5	1A	12	-500	$P_o = 10\text{W}$ ($f=700\text{MHz}$, $V_{cc}=18\text{V}$, $P_i=4\text{W}$)		1500*	13		159		
	" 1415	"	"	"	40	3.5	3A	25W ($T_c=25^\circ\text{C}$)	175	600	20	80	5	2A	12	-500	$P_o = 16\text{W}$ ($f=700\text{MHz}$, $V_{cc}=18\text{V}$, $P_i=7.5\text{W}$)		1200*	18		159		
★	" 1416	東芝	RF	"	55	5	50	200	150	0.1	30	350	6	2	6	-1	NF=2dB ($f=100\text{Hz}$, $V_{CE}=6\text{V}$, $I_E=-6.1\text{mA}$)		100*	3	45	195		
	" 1417	日立	RF. Conv. Mix. Osc	Si. P	20		30	100	125	1	10	100	6	1	6	-1			300*	1.4	$C_c \tau_{bb'}$ 24pS	37		
★	" 1418	"	"	Si. T	50	4	2A	20W ($T_c=25^\circ\text{C}$)	150	100	30	35~320	4	1A	4	-500			5*			267	2SA754 とコンプリ	
	" 1419	"	"	"	50	4	2A	20W ($T_c=25^\circ\text{C}$)	150	100	20	35~320	4	1A	4	-500			5*			268	2SA755 とコンプリ	
★	" 1420	富士通	RF	Si. EP	15	3	70	300	150	0.5	10	80	6	40	6	-40			6000*	1	25*	199		